BT139 series E

GENERAL DESCRIPTION

Glass passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

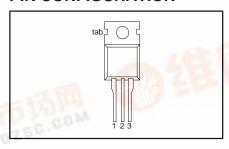
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500E 500 16 140	600E 600 16 140	800E 800 16 140	V A A

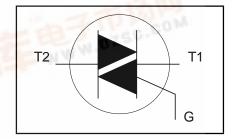
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

WWW.DZSC

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.	W	UNIT
V_{DRM}	Repetitive peak off-state voltages	A48	庭	-500 500 ¹	-600 600 ¹	-800 800	>
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}C$ full sine wave; $T_{j} = 25 ^{\circ}C$ prior to surge	-		16		A
		t = 20 ms	-		140		A A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 16.7 ms t = 10 ms $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-		150 98		A A ² s
	triggering	T2+ G+ T2+ G- T2- G- T2- G+		电	50 50 50 10		Α/μs Α/μs Α/μs Α/μs
I _{GM} V _{GM} P _{GM}	Peak gate current Peak gate voltage Peak gate power	-750 610 213	154	All an	2 5 5		V W
$\begin{bmatrix} P_{G(AV)} \\ T_{stg} \\ T_j \end{bmatrix}$	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -		0.5 150 125		O, O,

BT139 series E

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	1 1 1	- - 60	1.2 1.7 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
01		T2+ G+	-	2.5	10	mΑ
		T2+ G-	-	4.0	10	mΑ
		T2- G-	-	5.0	10	mΑ
		T2- G+	-	11	25	mΑ
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
		T2+ G-	-	3.2	30	mA
		T2+ G-	-	16	40	mA
		T2- G-	-	4.0	30	mA
		T2- G+	-	5.5	40	mA
l I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	4.0	30	mΑ
V _T	On-state voltage	$I_{T} = 20 \text{ A}$	-	1.2	1.6	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		0.7	1.5	V
1.		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 ^{\circ}\text{C}$	0.25	0.4		V.
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	mΑ

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C; exponential waveform; gate open circuit	-	50	-	V/μs
t _{gt}	Gate controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

BT139 series E

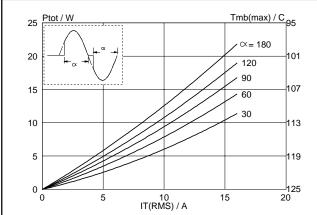


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

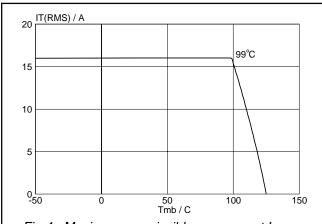


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

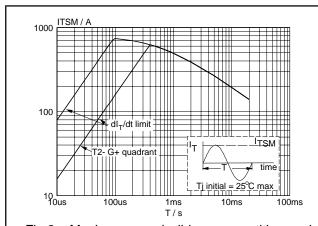


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

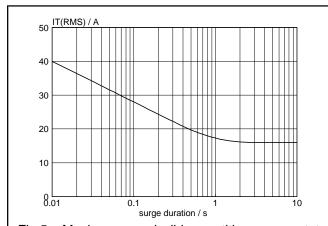


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 99 ^{\circ}\text{C}$.

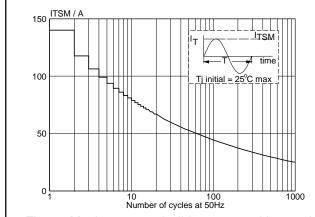


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

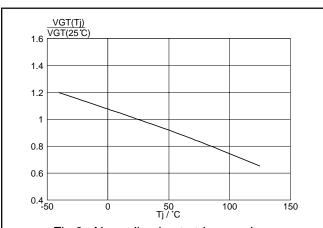
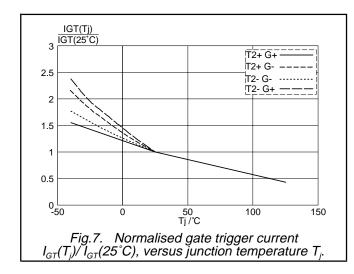


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_j .

BT139 series E



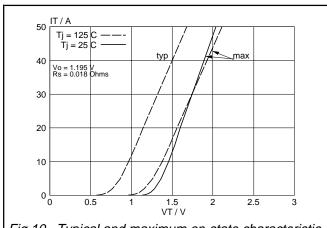


Fig.10. Typical and maximum on-state characteristic.

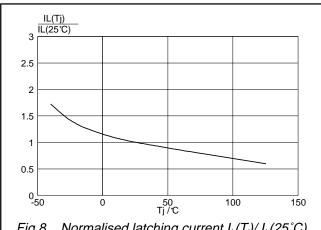


Fig.8. Normalised latching current $I_L(T_i)/I_L(25^{\circ}C)$, versus junction temperature T_i .

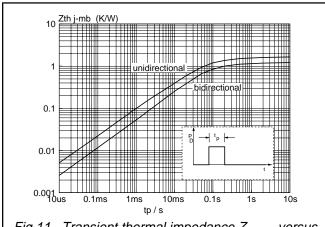


Fig.11. Transient thermal impedance $Z_{th j\text{-mb}}$, versus pulse width t_p .

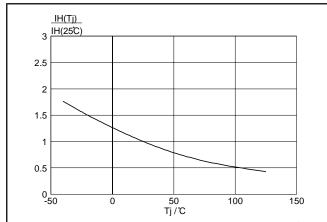


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_i .

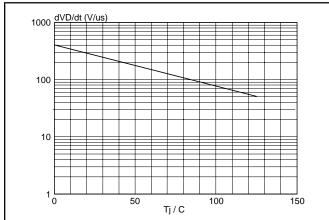
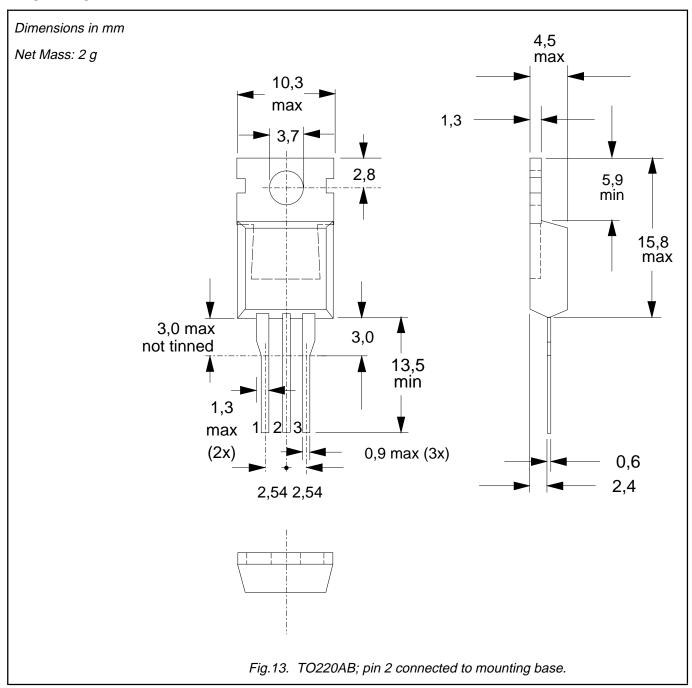


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j.

BT139 series E

MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for TO220 envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

BT139 series E

DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
1					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

© Philips Electronics N.V. 1997

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, it is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.